

1/4

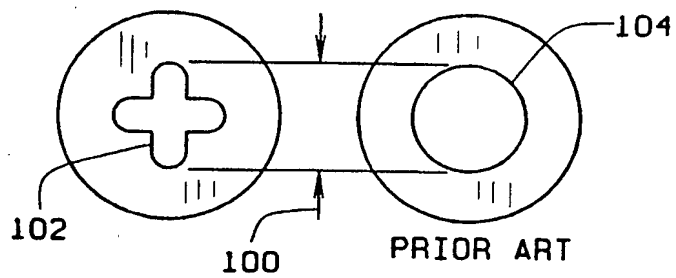


FIG. 1

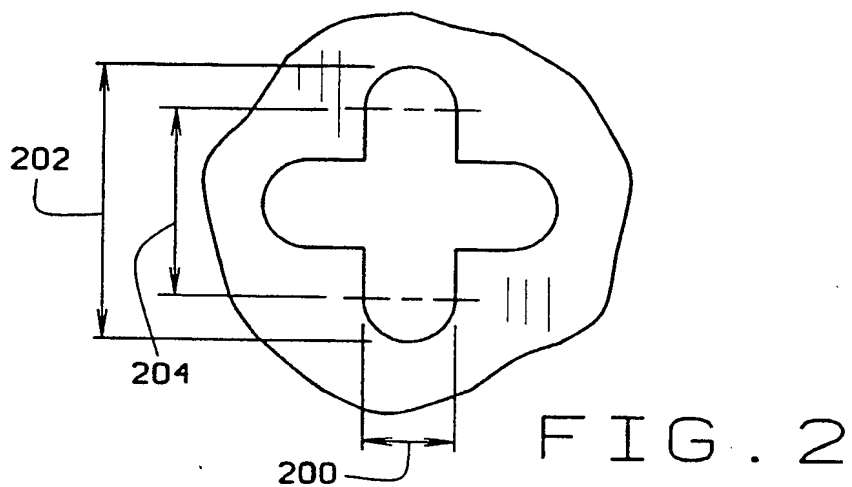


FIG. 2

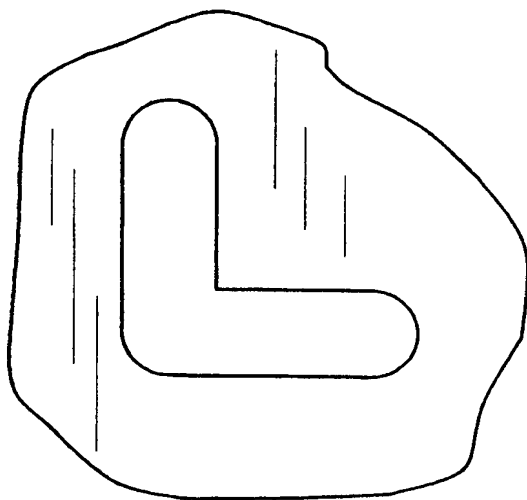


FIG. 3

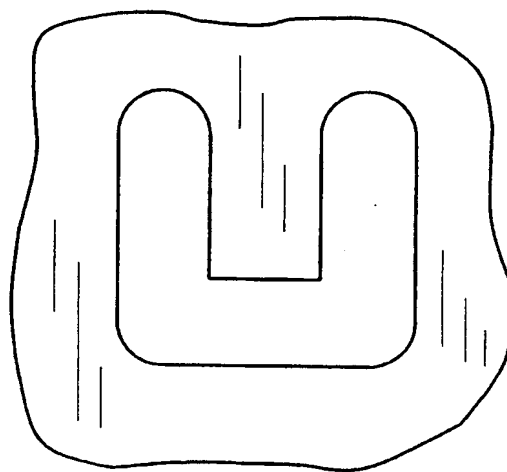


FIG. 4

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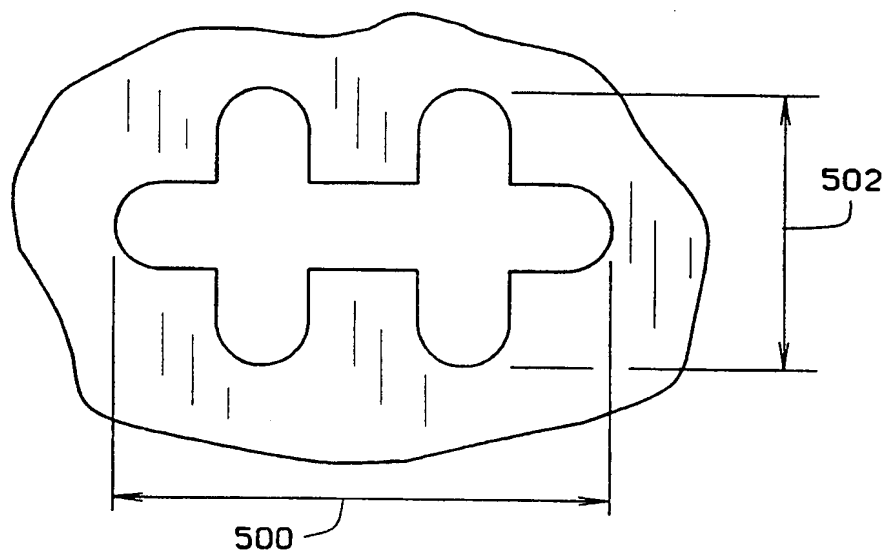


FIG. 5

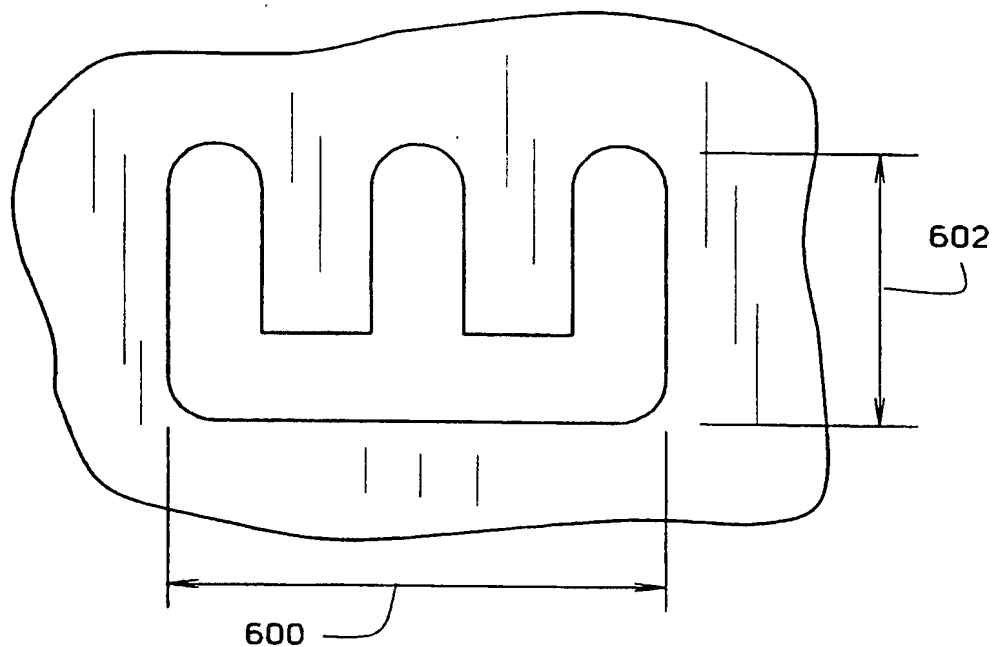


FIG. 6

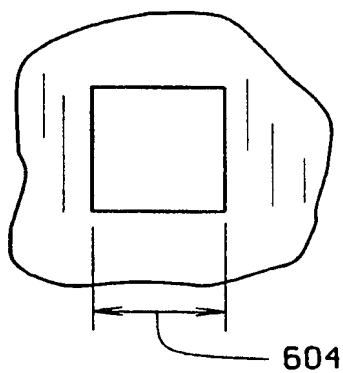


FIG. 6A

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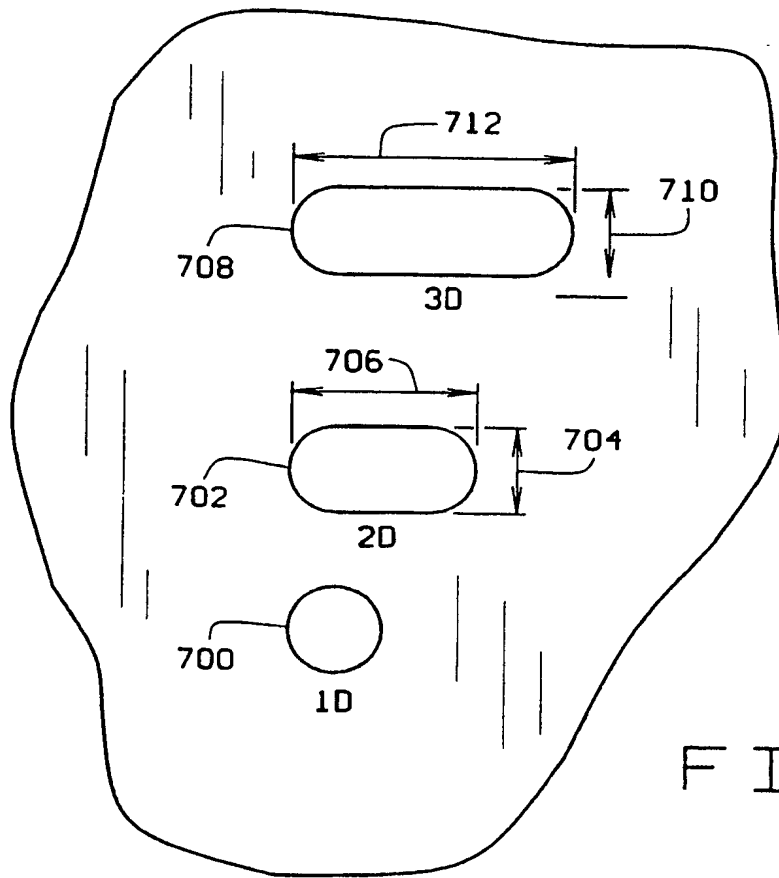


FIG. 7

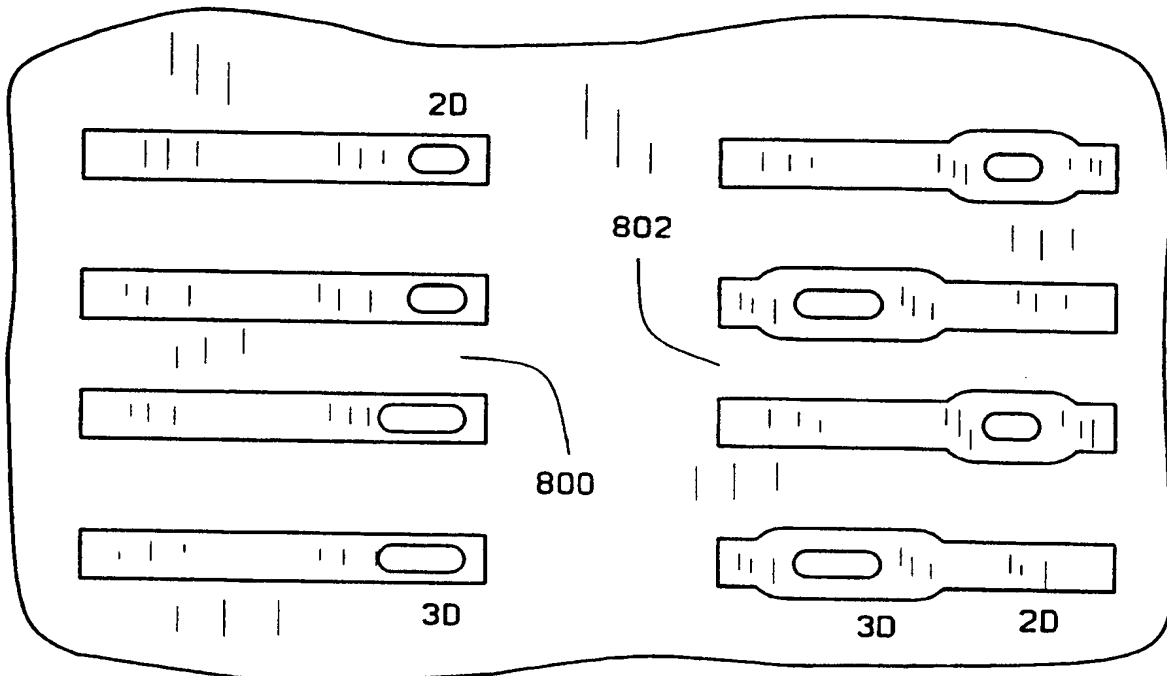
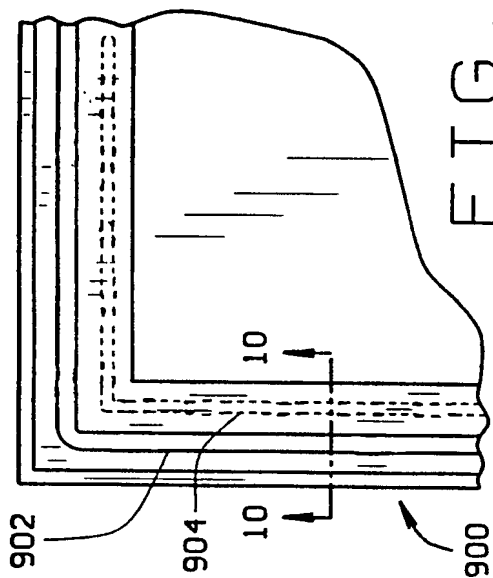


FIG. 8



This cross-sectional view shows a semiconductor device with a trench. The device includes a substrate 1002, a trench 1004, and a trench sidewall 1006. A layer 1108 is formed on the trench sidewall 1006. A layer 902 is formed on the substrate 1002 and the trench sidewall 1006. A layer 904 is formed on the layer 902. A layer 1000 is formed on the layer 904.

FIG. 10

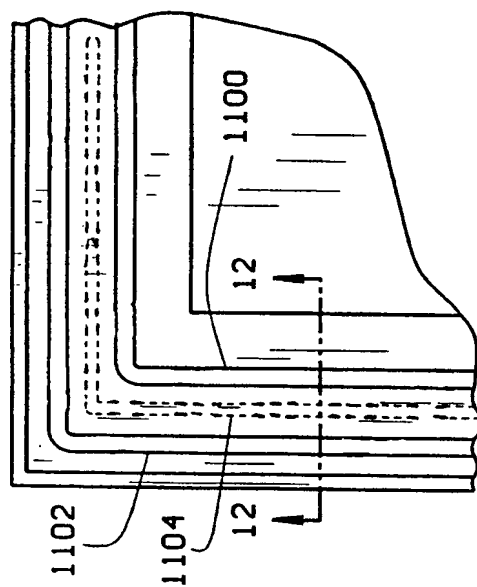


FIG. 11

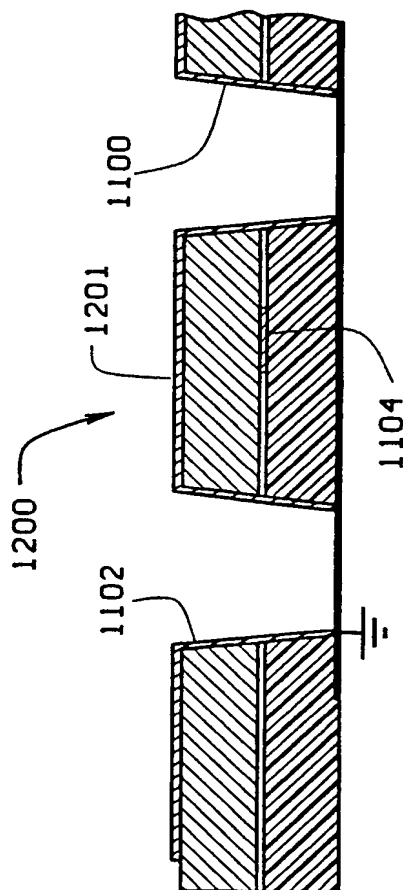


FIG. 12